

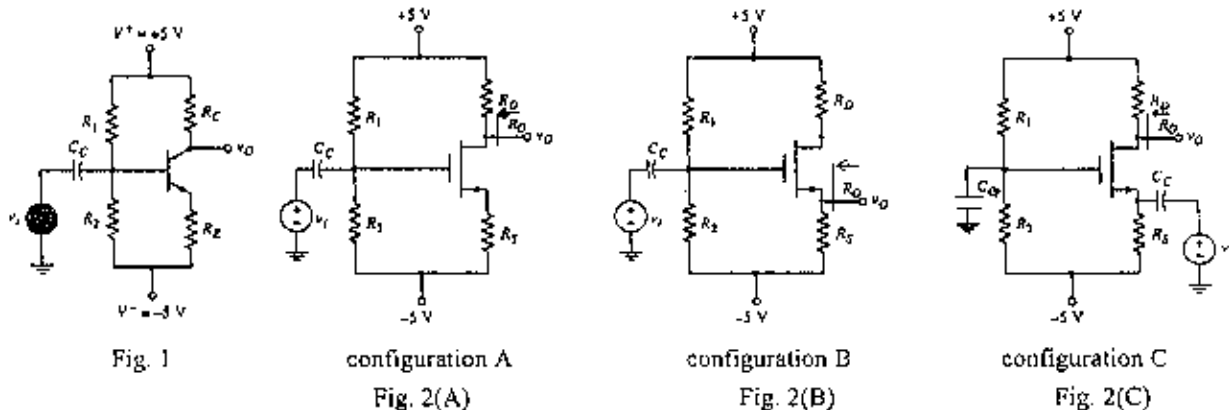
國立中央大學九十一學年度碩士班研究生入學試題卷

所別: 電機工程學系甲乙丙組 科目: 電子學 共 2 頁 第 1 頁
通訊工程研究所 丙組

1. 選擇題(15分, 答錯每題倒扣1分)

For the circuit shown in Fig. 1, let $R_C = 3\text{ k}\Omega$, $R_E = 1\text{ k}\Omega$, $\beta_F = 100$, $V_{BE(on)} = 0.7\text{ V}$, $V_{CE(sat)} = 0.3\text{ V}$, and Early voltage $V_A = \infty$. Four bias conditions are available: (A) $R_1 = 50\text{ k}\Omega$, and $R_2 = 50\text{ k}\Omega$ (B) $R_1 = 80\text{ k}\Omega$, $R_2 = 20\text{ k}\Omega$, (C) $R_1 = 20\text{ k}\Omega$, $R_2 = 80\text{ k}\Omega$, and (D) $R_1 = 70\text{ k}\Omega$, $R_2 = 30\text{ k}\Omega$.

- (1) Which bias condition(s) could be chosen such that this circuit could be used as a voltage amplifier. (5分, 複選)
- (2) Which bias condition could provide the maximum allowable output signal swing for a voltage amplifier? (5分)
- (3) Which bias condition(s) could be chosen such that this BJT is operated in saturation region. (5分, 複選題)



2. (15分, 答錯倒扣3分)

For the circuits shown in Fig.2, let $R_1 = 600\text{ k}\Omega$, $R_2 = 400\text{ k}\Omega$, $R_D = 5\text{ k}\Omega$, and $R_S = 1\text{ k}\Omega$, $\mu_n C_{ox} = 100\text{ }\mu\text{A/V}^2$, $(W/L)_n = 2.5\text{ }\mu\text{m}/1\text{ }\mu\text{m}$, $V_{TH} = 1\text{ V}$, and $V_A = \infty$, such that the MOSFET is biased to have a drain current $I_D = 1\text{ mA}$. Consider three amplifier configurations A, B, and C as shown in Fig. 2(A), 2(B), and 2(C), respectively.

- (1) Which configuration could provide the maximum voltage gain $A_v = v_o/v_i$? (3分) Please specify the value of A_v . (5分)
- (2) Which configuration could provide the minimum output resistance? (3分) Please specify the value of R_o . (4分)

3. (15分)

For the op-amp phase-shifter circuit as shown in Fig. 3

- (1) derive the transfer function $T(s)$ and find the corresponding zero and pole, (9分)
- (2) find the phase-shift at $\omega_0 = 1/RC$, (2分)
- (3) if the input frequency = 10^5 Hz and $C = 1.59\text{ nF}$, calculate the required values of R for phase-shift magnitudes of 30° , 60° , 120° , and 150° . (4分)

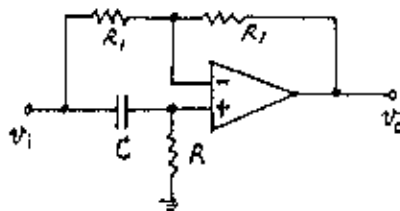


Fig. 3

注意: 背面有試題

4. (15分)

A ring oscillator of 5 inverters is constructed with the basic matched CMOS inverter. The transistor parameters are $V_{in} = -V_{ip} = 0.6\text{ V}$, $\mu_n C_{ox} = 100\text{ }\mu\text{A/V}^2$, $\mu_p C_{ox} = 40\text{ }\mu\text{A/V}^2$, $(W/L)_n = 1.2\text{ }\mu\text{m}/0.8\text{ }\mu\text{m}$, $(W/L)_p = 3\text{ }\mu\text{m}/0.8\text{ }\mu\text{m}$, $C_{ox} = 1.8\text{ fF}/\mu\text{m}^2$, $C_{gt} = 0.5\text{ fF}/\mu\text{m}$, and $C_{db} = 2.5\text{ fF}/\mu\text{m}$. C_W is negligible.

- (1) If the voltage supply $V_{DD} = 3.3\text{ V}$, estimate the equivalent load capacitance and propagation delay of an inverter stage, and the oscillation frequency of ring-oscillator. (12分)
- (2) If the voltage supply V_{DD} is reduced to 2.0 V , what would you expect the oscillation frequency of ring-oscillator to become? (3分)

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5. 選擇題(15分, 答錯每題倒扣1分)

Consider three amplifiers A, B, and C as shown in Fig. 5(a), 5(b), and 5(c), respectively. Assume all MOSFETs are operated in saturation region and of the same size, $C_{gs} = 2C_{gd}$, C_x is infinite, $I_1 = I_2 = I_3$, and $1/R$ is much smaller than MOSFETs' transconductance. Neglect channel length modulation effect and body effect. The gain responses of the three amplifiers are as shown in Fig. 5(d). Let the low frequency voltage gain (V_o/V_i) of the three amplifiers are A_1 , A_2 , and A_3 . The -3dB bandwidth of the three amplifiers are f_1 , f_2 , and f_3 . Which statement is correct?

(1)(5分) (a) $A_1 > A_2 > A_3$ (b) $A_3 > A_1 > A_2$ (c) $A_2 > A_3 > A_1$ (d) $A_1 > A_3 > A_2$ (e) $A_1 > A_2 = A_3$.

(2)(5分) (a) $f_1 > f_2 > f_3$ (b) $f_2 = f_3 > f_1$ (c) $f_2 > f_3 > f_1$ (d) $f_3 > f_2 > f_1$ (e) $f_1 > f_2 = f_3$.

(3)(5分) Adjust I_1 , I_2 , and I_3 such that the three amplifiers have the same voltage gain. In this case, assume all MOSFETs are operated in saturation region, which amplifier has the lowest DC power consumption?
 (a) Amplifier A (b) Amplifier B (c) Amplifier C.

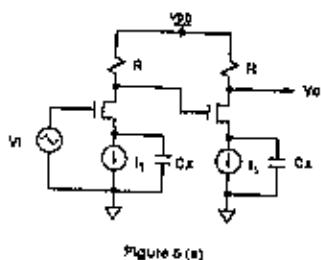


Figure 5(a)

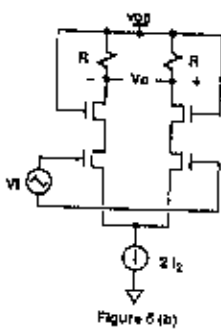


Figure 5(b)

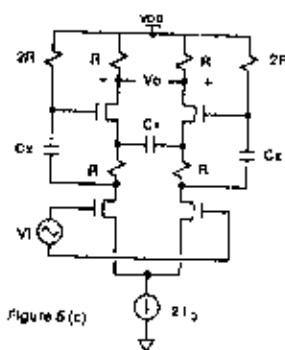


Figure 5(c)

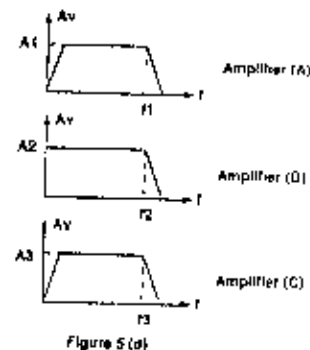


Figure 5(d)

6. (25分, 答錯每題倒扣1分)

Consider three circuits as shown in Fig. 6. Assume OPA is an ideal operational amplifier (gain = ∞), the saturation voltage of OP is 10 V and 0 V, $V_{th} = |V_{tp}| = 1\text{ V}$, $\mu_n C_{ox}(W/L)_{M1} = \mu_p C_{ox}(W/L)_{M2} = \mu_n C_{ox}(W/L)_{M3} = 8\text{ mA/V}^2$, $V_i = 4\text{ V}$.

(1)(5分) Which statement could be correct? (a) $V_{o1} = V_{o3}$ (b) $V_{o2} = V_{o3}$ (c) $V_{o1} = V_{o2}$

(2)(5分) What kind of feedback is utilized in amplifier Fig. 6(b)?
 (a) shunt-shunt (b) series-shunt (c) shunt-series (d) series-series

(3)(5分) What kind of feedback is utilized in Fig. 6(c)?
 (a) shunt-shunt (b) series-shunt (c) shunt-series (d) series-series

(4)(5分) $V_x = ?$ (a) 4 V (b) 5 V (c) 6 V (d) 7 V (e) 3 V

(5)(5分) If OPA gain = 100, g_{m3} is the transconductance of M3. In Fig. 6(c), to increase the output impedance R_o by adjusting W/L of M3, which approach could be useful?

(a) reduce the channel length of M3 while keeping g_{m3} unchanged (b) reduce the channel width of M3 while keeping the channel length unchanged (c) increase the channel width of M3 while keeping channel length unchanged.

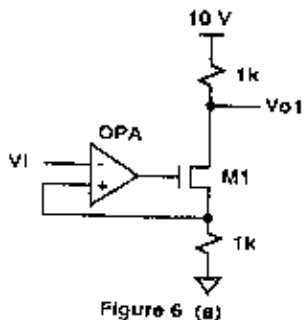


Figure 6(a)

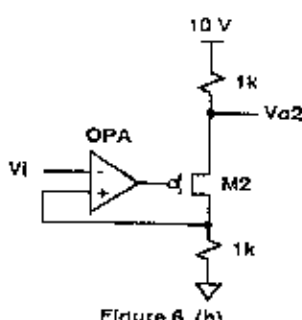


Figure 6(b)

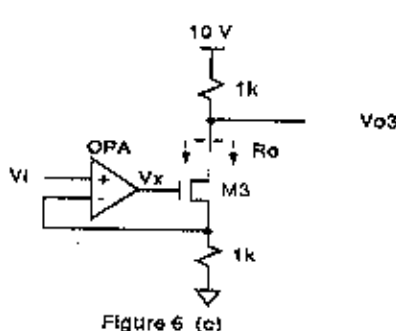


Figure 6(c)

參考用